



Description

The HSCB20D03 is the high cell density trenched P-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications.

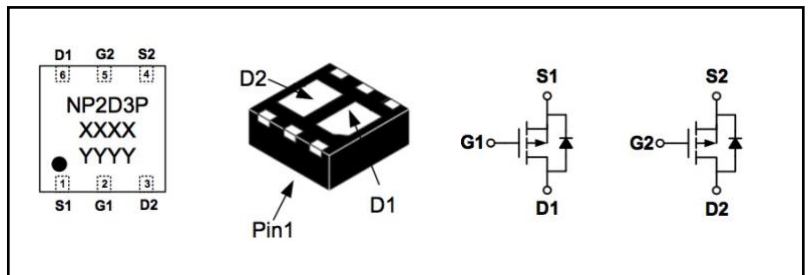
The HSCB20D03 meets the RoHS and Green Product requirement with full function reliability approved.

- Super Low Gate Charge
- Green Device Available
- Excellent Cdv/dt effect decline
- Advanced high cell density Trench technology

Product Summary

V_{DS}	-20	V
$R_{DS(ON),typ}$	90	mΩ
I_D	-3	A

DFN2*2-6L-D Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Limit	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D@T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-3	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-2	A
I_{DM}	Pulsed Drain Current ²	-12	A
$P_D@T_A=25^\circ C$	Total Power Dissipation ³	1.5	W
$P_D@T_A=70^\circ C$	Total Power Dissipation ³	0.95	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	100	$^\circ C/W$



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-20	---	---	V
ΔBV _{DSS} /ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C, I _D =-1mA	---	-0.01	---	V/°C
R _{DS(on)}	Static Drain-Source On-Resistance ²	V _{GS} =-4.5V, I _D =-3.0A	---	90	100	mΩ
		V _{GS} =-2.5V, I _D =-2.0A	---	110	130	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-0.5	-0.75	-1.2	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	2.98	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-16V, V _{GS} =0V, T _J =25°C	---	---	-1	uA
		V _{DS} =-16V, V _{GS} =0V, T _J =55°C	---	---	-5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±12V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =-5V, I _D =-2.8A	---	5	---	S
Q _g	Total Gate Charge (-4.5V)	V _{DS} =-10V, V _{GS} =-4.5V, I _D =-3A	---	3.3	---	nC
Q _{gs}	Gate-Source Charge		---	0.66	---	
Q _{gd}	Gate-Drain Charge		---	0.91	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =-10V, V _{GS} =-4.5V, R _G =60Ω I _D =-3A, R _L =10Ω	---	11	---	ns
T _r	Rise Time		---	6	---	
T _{d(off)}	Turn-Off Delay Time		---	23	---	
T _f	Fall Time		---	8	---	
C _{iss}	Input Capacitance	V _{DS} =-10V, V _{GS} =0V, f=1MHz	---	331	---	pF
C _{oss}	Output Capacitance		---	64	---	
C _{rss}	Reverse Transfer Capacitance		---	37	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,4}	V _G =V _D =0V, Force Current	---	---	-3	A
I _{SM}	Pulsed Source Current ^{2,4}		---	---	-12	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =-1A, T _J =25°C	---	---	-1	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



Typical Characteristics

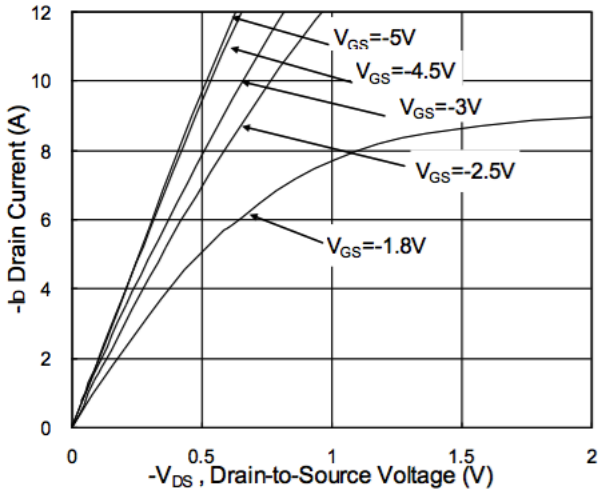


Fig.1 Typical Output Characteristics

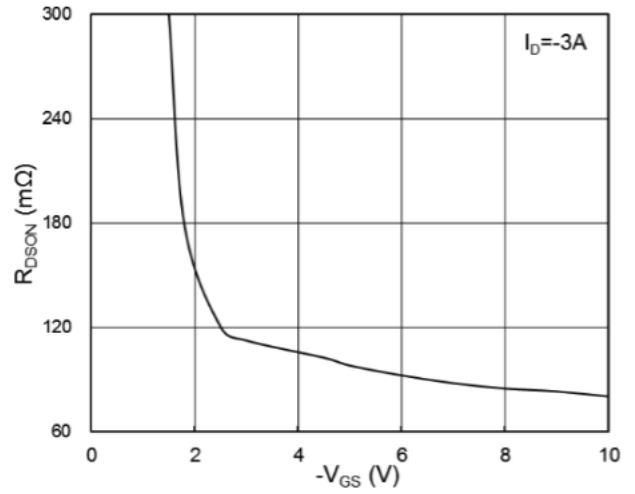


Fig.2 On-Resistance vs. G-S Voltage

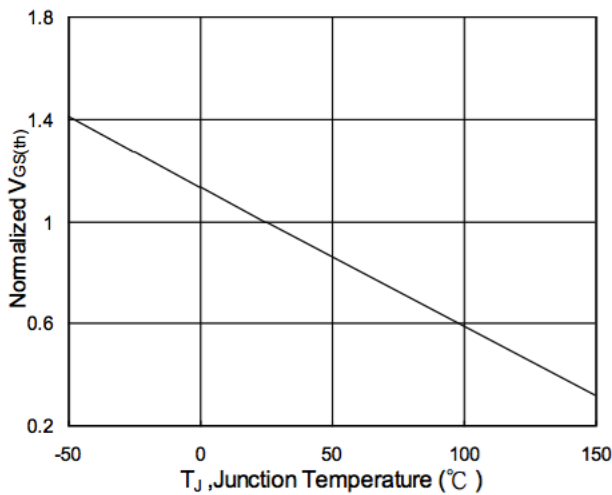
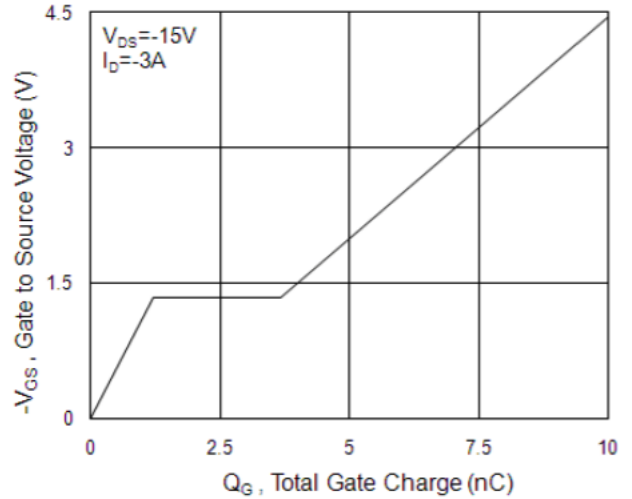
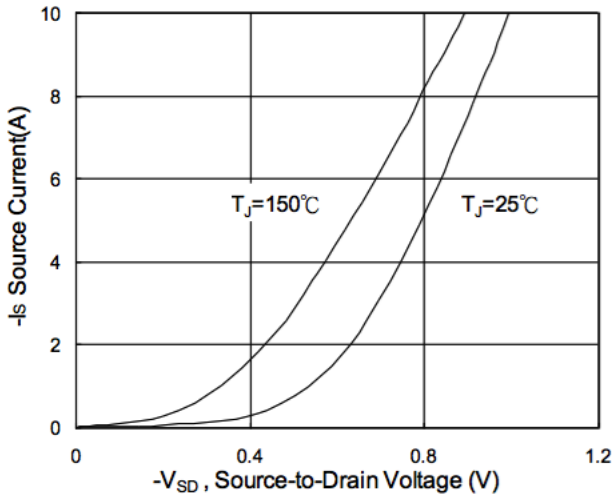


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

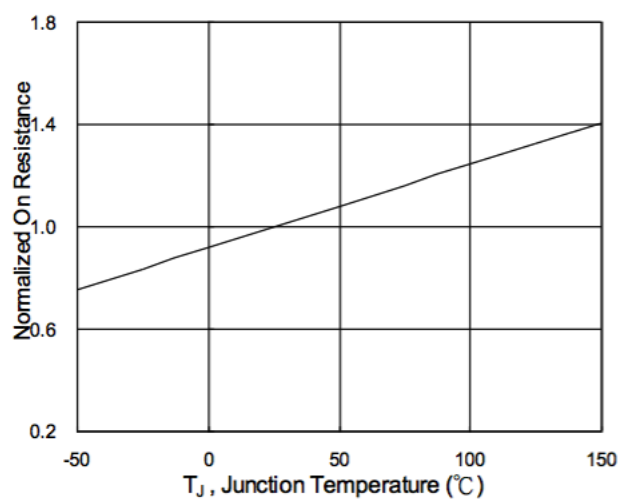


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

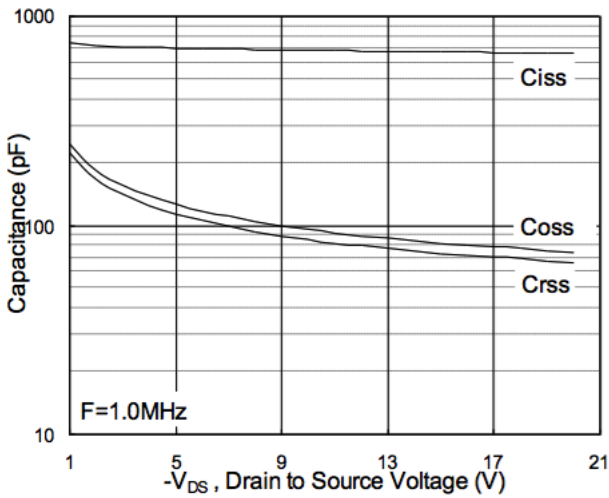


Fig.7 Capacitance

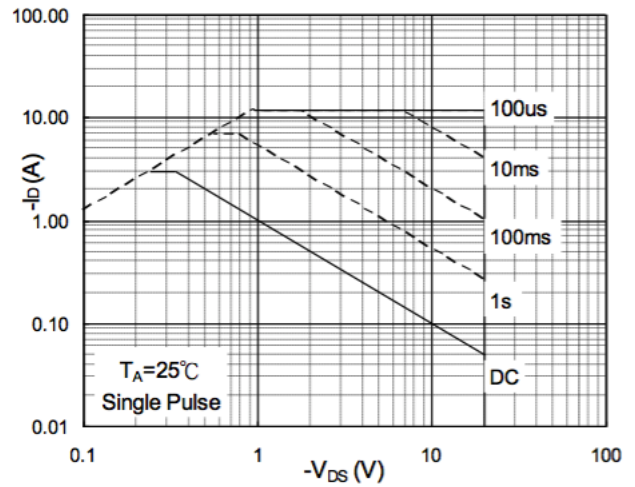


Fig.8 Safe Operating Area

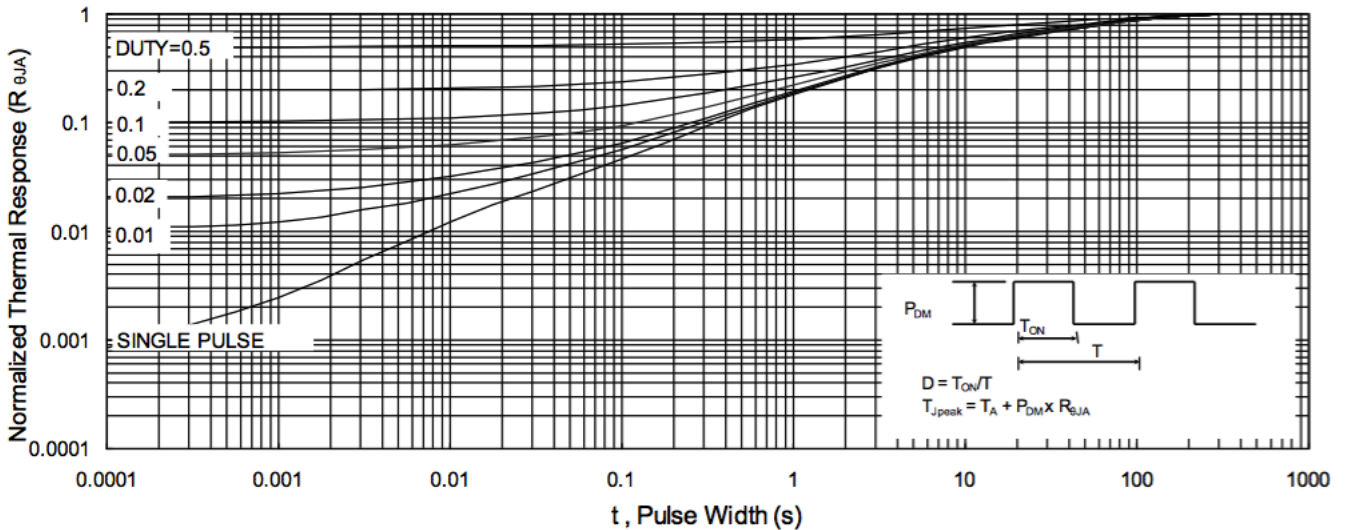


Fig.9 Normalized Maximum Transient Thermal Impedance

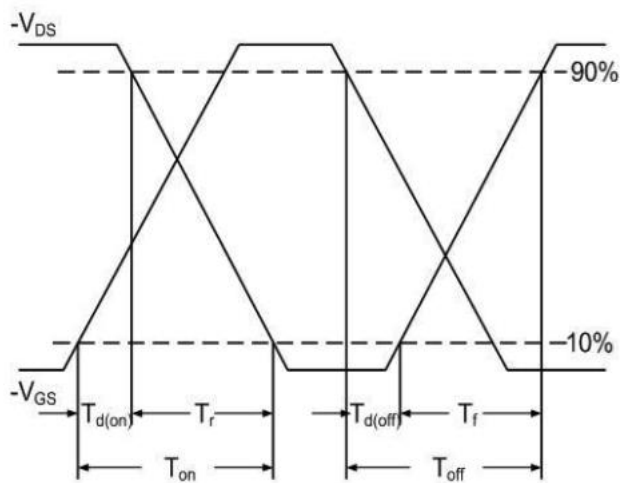


Fig.10 Switching Time Waveform

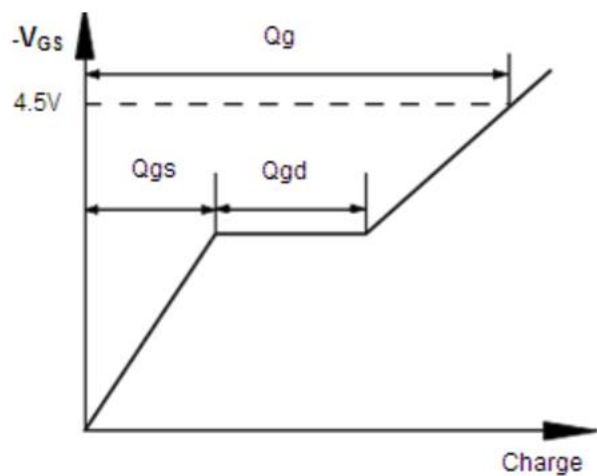
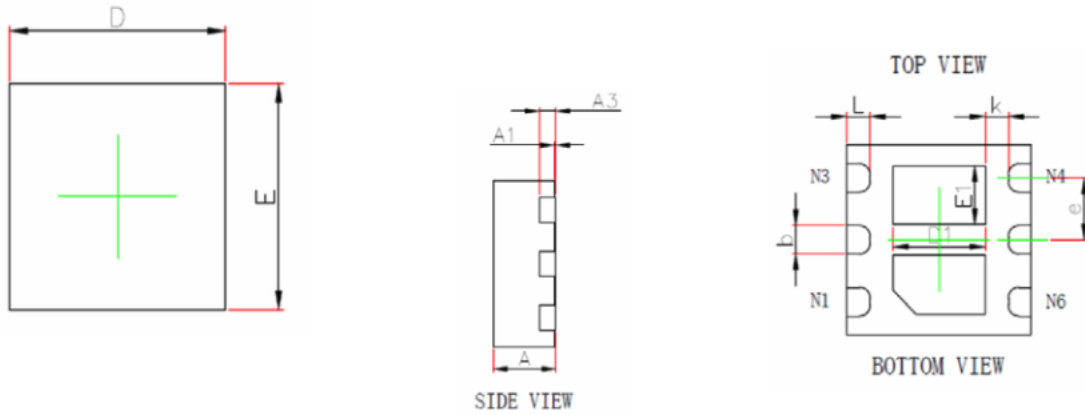


Fig.11 Gate Charge Waveform



Package Information

- DFN2*2-6L-D



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.800	0.028	0.031
A1	0.000	0.050	0.000	0.002
A3	0.203REF.		0.008REF.	
D	1.900	2.100	0.075	0.083
E	1.900	2.100	0.075	0.083
D1	0.900	1.100	0.035	0.043
E1	0.520	0.720	0.020	0.028
b	0.250	0.350	0.010	0.014
e	0.650TYP.		0.026TYP.	
k	0.200MIN.		0.008MIN.	
L	0.200	0.300	0.008	0.012